

JCT1640Z

Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	10	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W

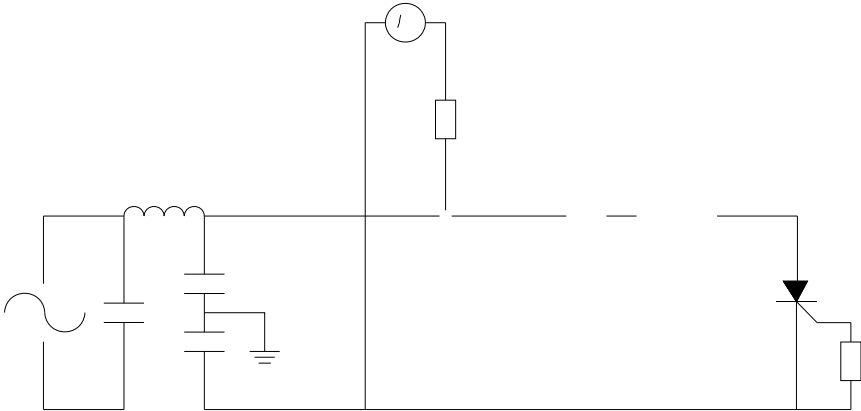
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FIG.1: Maximum power dissipation versus RMS on-state current



FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.




ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
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PACKAGE MECHANICAL DATA



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